

**KSA952**

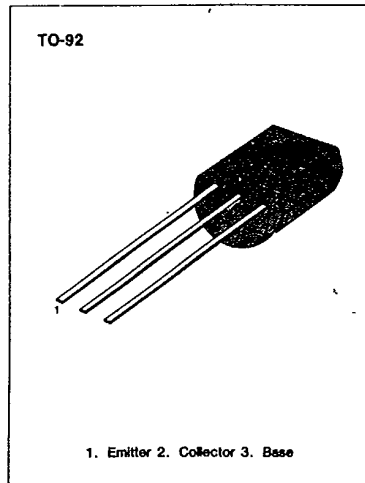
**PNP SILICON TRANSISTOR**

**GENERAL PURPOSE APPLICATIONS**  
**HIGH TOTAL POWER DISIPATION**  
**(PT=600 mW)**

High  $h_{FE}$  and LOW  $V_{CE(sat)}$

**ABSOLUTE MAXIMUM RATINGS ( $T_a=25^{\circ}C$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	-30	V
Collector-Emitter Voltage	$V_{CEO}$	-25	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-700	mA
Base Current	$I_B$	-150	mA
Collector Dissipation	$P_C$	600	mW
Junction Temperature	$T_J$	150	$^{\circ}C$
Storage Temperature	$T_{stg}$	-55~150	$^{\circ}C$



**ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}C$ )**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
* Base Emitter Voltage	$V_{BE}$	$V_{CE}=-6V, I_C=-10mA$	-600	-640	-700	mV
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=-30V, I_E=0$			-100	nA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$			-100	nA
* DC Current Gain	$h_{FE1}$	$V_{CE}=-1V, I_C=-100mA$	90	200	400	
	$h_{FE2}$	$V_{CE}=-1V, I_C=-700mA$	50	100		
* Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-700mA, I_B=-70mA$		-0.25	-0.6	V
* Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-700mA, I_B=-70mA$		-0.95	-1.2	V
Output Capacitance	$C_{ob}$	$V_{CB}=-6V, I_E=0, f=1MHz$		17	40	pF
Current Gain Bandwidth Product	$f_T$	$V_{CE}=-6V, I_E=10mA$	50	160		MHz

\* Pulse test:  $PW \leq 350\mu s$ , duty cycle  $\leq 2\%$  Pulsed

**$h_{FE1}$  CLASSIFICATION**

Classification	R	O	Y
$h_{FE1}$	90-180	135-270	200-400